## IN THE CLAIMS:

## 1.-7. (Canceled)

8. (Currently amended) A gate electrode, comprising:

a gate layer disposed above a substrate, said gate layer having a substantially level upper surface;

a conductive layer disposed over said gate layer, said conductive layer extending beyond edges of said gate layer;

thin first spacers disposed in contact with opposite sides of said gate layer and below said conductive layer; and

thick second spacers disposed in contact with said thin first spacers, each thick second spacer having a width which is constant in a direction parallel with said thin first spacers.

- 9. (Canceled)
- 10. (Previously presented) The gate electrode of claim 8, wherein said gate layer comprises polysilicon.
- 11. (Previously presented) The gate electrode of claim 10, wherein said conductive layer comprises polycide.
- 12. (Previously presented) The gate electrode of claim 8, wherein said thin first spacers comprise oxide.
- 13. (Canceled)



- 14. (Previously presented) The gate electrode of claim 11, wherein said polycide comprises titanium salicide (TiSi2).
- 15. 122. (Canceled)
- 123. (Previously presented) The gate electrode of claim 8, wherein said thick second spacers comprise nitride.
- 124. (Previously presented) The gate electrode of claim 8, wherein the thin first spacers are at least as high as the thick second spacers.
- 125. (Previously presented) The gate electrode of claim 8, wherein the thick second spacers are at least twice as thick as the thin first spacers.
- 126. (Previously presented) The gate electrode of claim 125, wherein the thick second spacers are between 300 and 2000 Å thick.
- 127. (Previously presented) The gate electrode of claim 126, wherein the thick second spacers are at least 800 Å thick.
- 128. (Previously presented) The gate electrode of claim 125, wherein the thick second spacers are at least 800/100 times as thick as the thin first spacers.

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